

ABSTRACT OF THE DISCLOSURE

Object: To provide a polishing composition which is capable of polishing a tantalum-containing compound at a high stock removal rate and whereby the copper surface after polishing is scarcely corroded, and to provide a
5 polishing process where dishing can be minimized.

Means to accomplish the object: A polishing composition comprising an abrasive, oxalic acid, an ethylenediamine derivative, a benzotriazole derivative and water and not
10 containing an oxidizing agent, and a polishing composition comprising an abrasive, oxalic acid, an ethylenediamine derivative, a benzotriazole derivative, water and hydrogen peroxide.

Further, a polishing process for forming a copper
15 printed wiring, which is a polishing process for a semiconductor device and which comprises a first polishing step wherein polishing is completed immediately before reaching a barrier layer while a copper layer still slightly remains, and second and third polishing
20 steps wherein the remaining copper layer and the barrier layer are polished, wherein in the second polishing step, a polishing composition containing hydrogen peroxide is used and all the copper layer to be removed, is removed by polishing, and then, in the third polishing step, a
25 polishing composition not containing hydrogen peroxide is used and all the barrier layer to be removed, is removed by polishing.

